Unit in mm

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

GT25Q101

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

• High Input Impedance

• High Speed : $t_f = 0.5 \mu s$ (Max.)

• Low Saturation Voltage: VCE (sat) = 4.0 V (Max.)

• Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

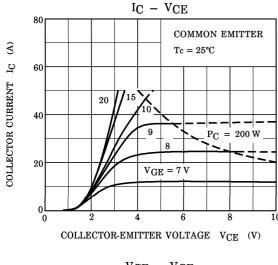
CHARACTERIS	SYMBOL	RATING	UNIT		
Collector-Emitter Voltage		v_{CES}	1200	V	
Gate-Emitter Voltage		v_{GES}	±20	V	
Collector Current	DC	$I_{\mathbf{C}}$	25	A	
Collector Current	1ms	I_{CP}	50		
Collector Power Dissipation (Tc=25°C)		PC	200	W	
Junction Temperature		T_{j}	150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	

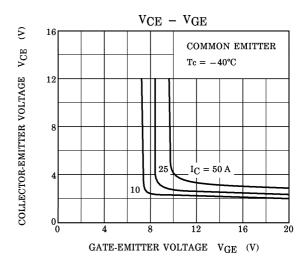
Weight: 9.75 g

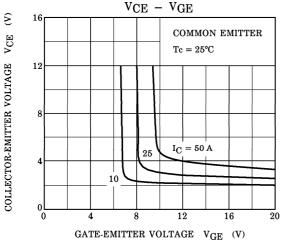
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

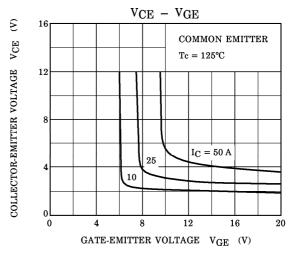
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage	Current	$I_{ ext{GES}}$	$V_{GE} = \pm 20 V, V_{CE} = 0$		_	±500	nA
Collector Cut-	off Current	ICES	$V_{CE} = 1200 \text{ V}, V_{GE} = 0$	_	_	1.0	mA
Gate-Emitter	Cut-off Voltage	V _{GE} (OFF)	$I_{\mathrm{C}}=25\mathrm{mA},~\mathrm{V_{\mathrm{CE}}}=5\mathrm{V}$	3.0	_	6.0	V
Collector-Emi		V _{CE} (sat)	$I_{C} = 25 \text{ A}, \text{ V}_{GE} = 15 \text{ V}$	_	3.0	4.0	V
Input Capacitance		Cies	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$		3200	_	pF
Switching Time	Rise Time	t _r	$\begin{array}{c c} V_{\text{OUT}} \\ V_{\text{IN}} \\ V_{\text{OUT}} \\ V_{\text{OUT}}$	1	0.2	0.6	
	Turn-on Time	ton		_	0.3	0.8	
	Fall Time	t_f		_	0.3	0.5	μ s
	Turn-off Time	$t_{ m off}$		_	0.8	1.5	

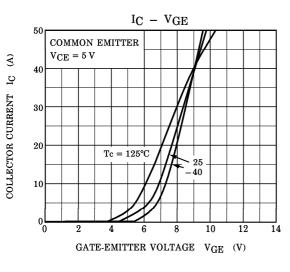
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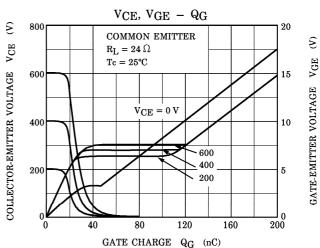




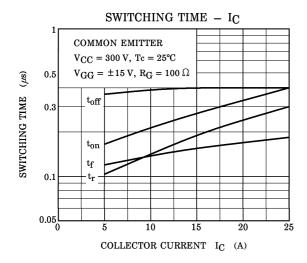


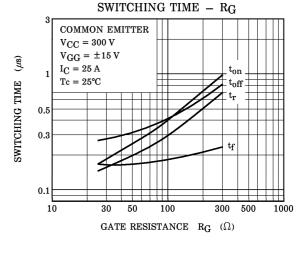


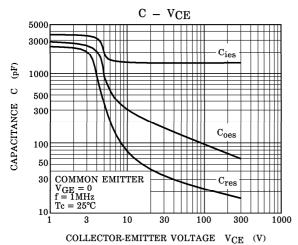


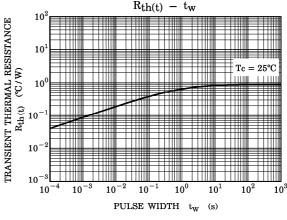


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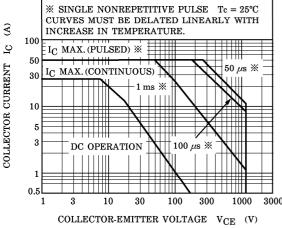


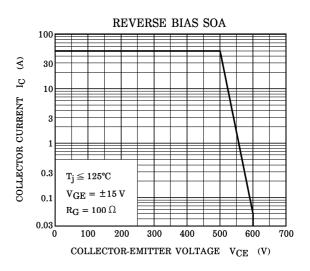












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